

## The Transition of Type-I to Type-II SiC/GaN Heterostructure by external strain

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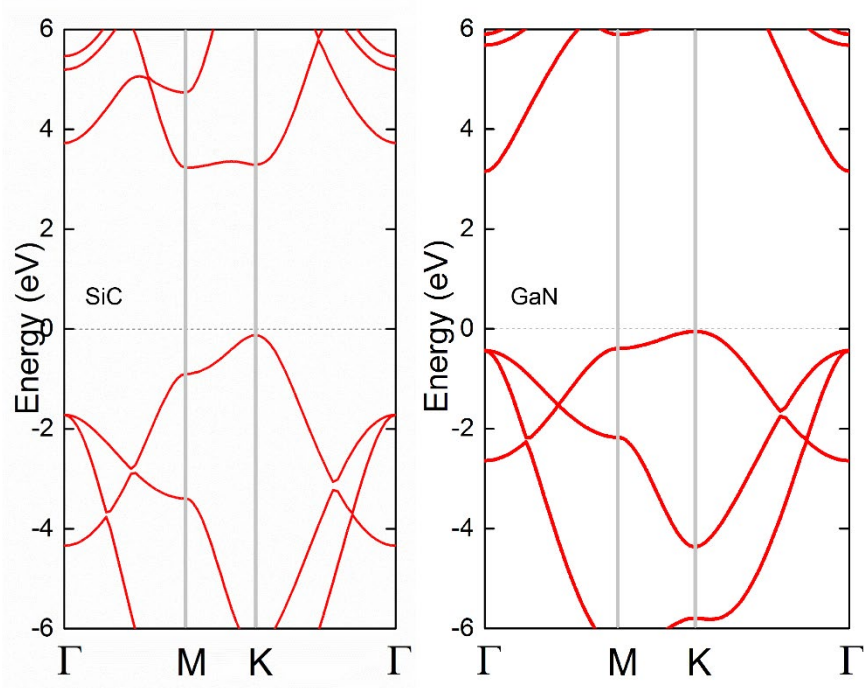
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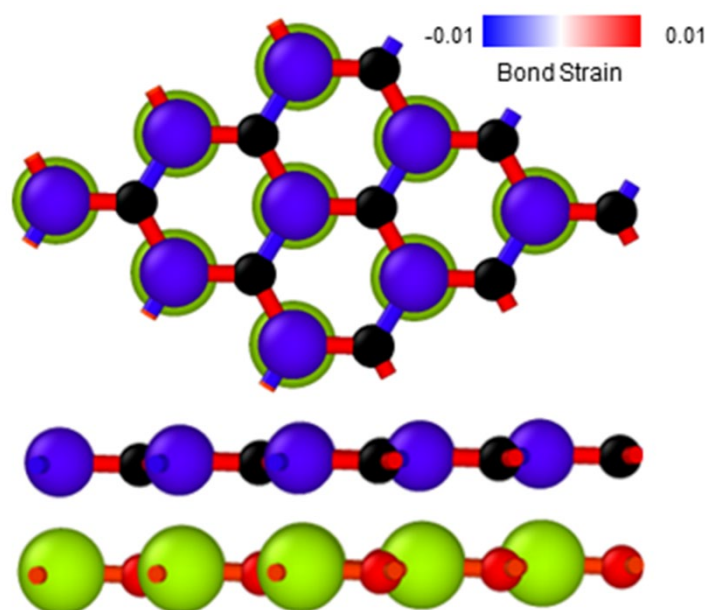
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**Figure S1.** The band structure of the SiC and GaN monolayers calculated by HSE06 function.



**Figure S2.** The bond strain of the SiC and GaN monolayers.